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PATENT <sup>B</sup>

#25-000

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Yuanning Chen, et al.

Serial No.: 09/597,076

Filed: June 20, 2000

For: TWO-STEP OXIDATION PROCESS FOR OXIDIZING A SILICON SUBSTRATE WHEREIN THE FIRST STEP IS CARRIED OUT AT A TEMPERATURE BELOW THE VISCOELASTIC TEMPERATURE OF SILICON DIOXIDE AND THE SECOND STEP IS CARRIED OUT AT A TEMPERATURE ABOVE THE VISCOELASTIC TEMPERATURE

Group: 2813

Examiner: Kielin, Erik J.

Date Mailed: November 15, 2002

Commissioner for Patents  
Washington, D. C. 20231

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Sir:

LETTER TO OFFICIAL DRAFTSMAN

Transmitted herewith are Nine sheets of formal drawings to be substituted for the informal drawings initially filed in the above-identified application for patent.

Respectfully submitted,

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